

Amendments to the Specification:

Please replace the title as follows:

~~MAGNETORESISTIVE DEVICE CAPABLE OF PREVENTING A SENSE CURRENT  
FROM FLOWING INTO DEAD REGIONS OF A MAGNETORESISTIVE ELEMENT,  
AND THIN FILM MAGNETIC HEAD, HEAD GIMBAL ASSEMBLY AND HARD DISK  
DRIVE UTILIZING THE SAME METHOD OF MANUFACTURING  
MAGNETORESISTIVE DEVICE CAPABLE OF PREVENTING A SENSE CURRENT  
FROM FLOWING INTO DEAD REGIONS OF A MAGNETORESISTIVE ELEMENT,  
AND METHOD OF MANUFACTURING THIN-FILM MAGNETIC HEAD~~

Please add the following paragraph between the title and the first line of text as follows:

PK 2/28/06  
This is a Division of Application No. 09/920,821 filed August 3, 2001. The entire disclosure of the prior application is hereby incorporated by reference herein in its entirety. <sup>now U.S. PAT. 6,657,826</sup>

Please replace the paragraph beginning on page 14, line 20 to page 15, line 3, with the following rewritten paragraph:

In the manufacturing method, as shown in FIG. 6A and FIG. 6B, an insulating layer 2 made of an insulating material such as alumina ( $\text{Al}_2\text{O}_3$ ) or silicon dioxide ( $\text{SiO}_2$ ) whose thickness is 1 to 20  $\mu\text{m}$ , for example, is formed through sputtering, for example, on a substrate 1 made of a ceramic material such as aluminum oxide and titanium carbide ( $\text{Al}_2\text{O}_3\text{-TiC}$ ). On the insulating layer 2 a bottom shield layer 3 having a thickness of 0.1 to 5  $\mu\text{m}$ , for example, is formed for making a read head. The bottom shield layer 3 is made of a magnetic material such as ~~FeAlSiFeAlSi~~, NiFe, CoFe, CoFeNi, FeN, FeZrN, FeTaN, CoZrNb, or CoZrTa. The bottom shield layer 3 is formed through sputtering or plating.